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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	540
Number of Logic Elements/Cells	4320
Total RAM Bits	94208
Number of I/O	104
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	132-LFBGA, CSPBGA
Supplier Device Package	132-CSPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-4000he-6mg132i

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MachXO2 Family Data Sheet Architecture

March 2016

Data Sheet DS1035

Architecture Overview

The MachXO2 family architecture contains an array of logic blocks surrounded by Programmable I/O (PIO). The larger logic density devices in this family have sysCLOCK[™] PLLs and blocks of sysMEM Embedded Block RAM (EBRs). Figure 2-1 and Figure 2-2 show the block diagrams of the various family members.





Note: MachXO2-256, and MachXO2-640/U are similar to MachXO2-1200. MachXO2-256 has a lower LUT count and no PLL or EBR blocks. MachXO2-640 has no PLL, a lower LUT count and two EBR blocks. MachXO2-640U has a lower LUT count, one PLL and seven EBR blocks.

Figure 2-2. Top View of the MachXO2-4000 Device



Note: MachXO2-1200U, MachXO2-2000/U and MachXO2-7000 are similar to MachXO2-4000. MachXO2-1200U and MachXO2-2000 have a lower LUT count, one PLL, and eight EBR blocks. MachXO2-2000U has a lower LUT count, two PLLs, and 10 EBR blocks. MachXO2-7000 has a higher LUT count, two PLLs, and 26 EBR blocks.

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ROM Mode

ROM mode uses the LUT logic; hence, slices 0-3 can be used in ROM mode. Preloading is accomplished through the programming interface during PFU configuration.

For more information on the RAM and ROM modes, please refer to TN1201, Memory Usage Guide for MachXO2 Devices.

Routing

There are many resources provided in the MachXO2 devices to route signals individually or as buses with related control signals. The routing resources consist of switching circuitry, buffers and metal interconnect (routing) segments.

The inter-PFU connections are made with three different types of routing resources: x1 (spans two PFUs), x2 (spans three PFUs) and x6 (spans seven PFUs). The x1, x2, and x6 connections provide fast and efficient connections in the horizontal and vertical directions.

The design tools take the output of the synthesis tool and places and routes the design. Generally, the place and route tool is completely automatic, although an interactive routing editor is available to optimize the design.

Clock/Control Distribution Network

Each MachXO2 device has eight clock inputs (PCLK [T, C] [Banknum]_[2..0]) – three pins on the left side, two pins each on the bottom and top sides and one pin on the right side. These clock inputs drive the clock nets. These eight inputs can be differential or single-ended and may be used as general purpose I/O if they are not used to drive the clock nets. When using a single ended clock input, only the PCLKT input can drive the clock tree directly.

The MachXO2 architecture has three types of clocking resources: edge clocks, primary clocks and secondary high fanout nets. MachXO2-640U, MachXO2-1200/U and higher density devices have two edge clocks each on the top and bottom edges. Lower density devices have no edge clocks. Edge clocks are used to clock I/O registers and have low injection time and skew. Edge clock inputs are from PLL outputs, primary clock pads, edge clock bridge outputs and CIB sources.

The eight primary clock lines in the primary clock network drive throughout the entire device and can provide clocks for all resources within the device including PFUs, EBRs and PICs. In addition to the primary clock signals, MachXO2 devices also have eight secondary high fanout signals which can be used for global control signals, such as clock enables, synchronous or asynchronous clears, presets, output enables, etc. Internal logic can drive the global clock network for internally-generated global clocks and control signals.

The maximum frequency for the primary clock network is shown in the MachXO2 External Switching Characteristics table.

The primary clock signals for the MachXO2-256 and MachXO2-640 are generated from eight 17:1 muxes The available clock sources include eight I/O sources and 9 routing inputs. Primary clock signals for the MachXO2-640U, MachXO2-1200/U and larger devices are generated from eight 27:1 muxes The available clock sources include eight I/O sources, 11 routing inputs, eight clock divider inputs and up to eight sysCLOCK PLL outputs.



The EBR memory supports three forms of write behavior for single or dual port operation:

- 1. **Normal** Data on the output appears only during the read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
- 2. Write Through A copy of the input data appears at the output of the same port. This mode is supported for all data widths.
- 3. Read-Before-Write When new data is being written, the old contents of the address appears at the output.

FIFO Configuration

The FIFO has a write port with data-in, CEW, WE and CLKW signals. There is a separate read port with data-out, RCE, RE and CLKR signals. The FIFO internally generates Almost Full, Full, Almost Empty and Empty Flags. The Full and Almost Full flags are registered with CLKW. The Empty and Almost Empty flags are registered with CLKR. Table 2-7 shows the range of programming values for these flags.

Table 2-7. Programmable FIFO Flag Ranges

Flag Name	Programming Range
Full (FF)	1 to max (up to 2^{N} -1)
Almost Full (AF)	1 to Full-1
Almost Empty (AE)	1 to Full-1
Empty (EF)	0

N = Address bit width.

The FIFO state machine supports two types of reset signals: RST and RPRST. The RST signal is a global reset that clears the contents of the FIFO by resetting the read/write pointer and puts the FIFO flags in their initial reset state. The RPRST signal is used to reset the read pointer. The purpose of this reset is to retransmit the data that is in the FIFO. In these applications it is important to keep careful track of when a packet is written into or read from the FIFO.

Memory Core Reset

The memory core contains data output latches for ports A and B. These are simple latches that can be reset synchronously or asynchronously. RSTA and RSTB are local signals, which reset the output latches associated with port A and port B respectively. The Global Reset (GSRN) signal resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-9.



Figure 2-9. Memory Core Reset



For further information on the sysMEM EBR block, please refer to TN1201, Memory Usage Guide for MachXO2 Devices.

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 2-10. The GSR input to the EBR is always asynchronous.

Figure 2-10. EBR Asynchronous Reset (Including GSR) Timing Diagram

Reset	
Clock	
Clock Enable	

If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of 1/f_{MAX} (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device wake up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM, ROM and FIFO implementations. For the EBR FIFO mode, the GSR signal is always enabled and the WE and RE signals act like the clock enable signals in Figure 2-10. The reset timing rules apply to the RPReset input versus the RE input and the RST input versus the WE and RE inputs. Both RST and RPReset are always asynchronous EBR inputs. For more details refer to TN1201, Memory Usage Guide for MachXO2 Devices.

Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.



Figure 2-11. Group of Four Programmable I/O Cells



Notes:

1. Input gearbox is available only in PIC on the bottom edge of MachXO2-640U, MachXO2-1200/U and larger devices. 2. Output gearbox is available only in PIC on the top edge of MachXO2-640U, MachXO2-1200/U and larger devices.



Figure 2-12. MachXO2 Input Register Block Diagram (PIO on Left, Top and Bottom Edges)



Right Edge

The input register block on the right edge is a superset of the same block on the top, bottom, and left edges. In addition to the modes described above, the input register block on the right edge also supports DDR memory mode.

In DDR memory mode, two registers are used to sample the data on the positive and negative edges of the modified DQS (DQSR90) in the DDR Memory mode creating two data streams. Before entering the core, these two data streams are synchronized to the system clock to generate two data streams.

The signal DDRCLKPOL controls the polarity of the clock used in the synchronization registers. It ensures adequate timing when data is transferred to the system clock domain from the DQS domain. The DQSR90 and DDRCLKPOL signals are generated in the DQS read-write block.

Figure 2-13. MachXO2 Input Register Block Diagram (PIO on Right Edge)









Tri-state Register Block

The tri-state register block registers tri-state control signals from the core of the device before they are passed to the sysIO buffers. The block contains a register for SDR operation. In SDR, TD input feeds one of the flip-flops that then feeds the output.

The tri-state register blocks on the right edge contain an additional register for DDR memory operation. In DDR memory mode, the register TS input is fed into another register that is clocked using the DQSW90 signal. The output of this register is used as a tri-state control.

Input Gearbox

Each PIC on the bottom edge has a built-in 1:8 input gearbox. Each of these input gearboxes may be programmed as a 1:7 de-serializer or as one IDDRX4 (1:8) gearbox or as two IDDRX2 (1:4) gearboxes. Table 2-9 shows the gearbox signals.

Name	I/O Type	Description
D	Input	High-speed data input after programmable delay in PIO A input register block
ALIGNWD	Input	Data alignment signal from device core
SCLK	Input	Slow-speed system clock
ECLK[1:0]	Input	High-speed edge clock
RST	Input	Reset
Q[7:0]	Output	Low-speed data to device core: Video RX(1:7): Q[6:0] GDDRX4(1:8): Q[7:0] GDDRX2(1:4)(IOL-A): Q4, Q5, Q6, Q7 GDDRX2(1:4)(IOL-C): Q0, Q1, Q2, Q3



DDR Memory Support

Certain PICs on the right edge of MachXO2-640U, MachXO2-1200/U and larger devices, have additional circuitry to allow the implementation of DDR memory interfaces. There are two groups of 14 or 12 PIOs each on the right edge with additional circuitry to implement DDR memory interfaces. This capability allows the implementation of up to 16-bit wide memory interfaces. One PIO from each group contains a control element, the DQS Read/Write Block, to facilitate the generation of clock and control signals (DQSR90, DQSW90, DDRCLKPOL and DATAVALID). These clock and control signals are distributed to the other PIO in the group through dedicated low skew routing.

DQS Read Write Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces a PLL is used for this adjustment. However, in DDR memories the clock (referred to as DQS) is not free-running so this approach cannot be used. The DQS Read Write block provides the required clock alignment for DDR memory interfaces. DQSR90 and DQSW90 signals are generated by the DQS Read Write block from the DQS input.

In a typical DDR memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the read cycle) is unknown. The MachXO2 family contains dedicated circuits to transfer data between these domains. To prevent set-up and hold violations, at the domain transfer between DQS (delayed) and the system clock, a clock polarity selector is used. This circuit changes the edge on which the data is registered in the synchronizing registers in the input register block. This requires evaluation at the start of each read cycle for the correct clock polarity. Prior to the read operation in DDR memories, DQS is in tri-state (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit in the DQS Read Write block detects the first DQS rising edge after the preamble state and generates the DDRCLKPOL signal. This signal is used to control the polarity of the clock to the synchronizing registers.

The temperature, voltage and process variations of the DQS delay block are compensated by a set of calibration signals (6-bit bus) from a DLL on the right edge of the device. The DLL loop is compensated for temperature, voltage and process variations by the system clock and feedback loop.

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS, TTL, PCI, SSTL, HSTL, LVDS, BLVDS, MLVDS and LVPECL.

Each bank is capable of supporting multiple I/O standards. In the MachXO2 devices, single-ended output buffers, ratioed input buffers (LVTTL, LVCMOS and PCI), differential (LVDS) and referenced input buffers (SSTL and HSTL) are powered using I/O supply voltage (V_{CCIO}). Each sysIO bank has its own V_{CCIO} . In addition, each bank has a voltage reference, V_{REF} which allows the use of referenced input buffers independent of the bank V_{CCIO} .

MachXO2-256 and MachXO2-640 devices contain single-ended ratioed input buffers and single-ended output buffers with complementary outputs on all the I/O banks. Note that the single-ended input buffers on these devices do not contain PCI clamps. In addition to the single-ended I/O buffers these two devices also have differential and referenced input buffers on all I/Os. The I/Os are arranged in pairs, the two pads in the pair are described as "T" and "C", where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.



Figure 2-21. PC Core Block Diagram



Table 2-15 describes the signals interfacing with the I²C cores.

 Table 2-15.
 PC Core Signal Description

Signal Name	I/O	Description
i2c_scl	Bi-directional	Bi-directional clock line of the I ² C core. The signal is an output if the I ² C core is in master mode. The signal is an input if the I ² C core is in slave mode. MUST be routed directly to the pre-assigned I/O of the chip. Refer to the Pinout Information section of this document for detailed pad and pin locations of I ² C ports in each MachXO2 device.
i2c_sda	Bi-directional	Bi-directional data line of the I ² C core. The signal is an output when data is transmitted from the I ² C core. The signal is an input when data is received into the I ² C core. MUST be routed directly to the pre-assigned I/O of the chip. Refer to the Pinout Information section of this document for detailed pad and pin locations of I ² C ports in each MachXO2 device.
i2c_irqo	Output	Interrupt request output signal of the I ² C core. The intended usage of this signal is for it to be connected to the WISHBONE master controller (i.e. a microcontroller or state machine) and request an interrupt when a specific condition is met. These conditions are described with the I ² C register definitions.
cfg_wake	Output	Wake-up signal – To be connected only to the power module of the MachXO2 device. The signal is enabled only if the "Wakeup Enable" feature has been set within the EFB GUI, I^2C Tab.
cfg_stdby	Output	Stand-by signal – To be connected only to the power module of the MachXO2 device. The signal is enabled only if the "Wakeup Enable" feature has been set within the EFB GUI, I^2C Tab.

Hardened SPI IP Core

Every MachXO2 device has a hard SPI IP core that can be configured as a SPI master or slave. When the IP core is configured as a master it will be able to control other SPI enabled chips connected to the SPI bus. When the core is configured as the slave, the device will be able to interface to an external SPI master. The SPI IP core on MachXO2 devices supports the following functions:

- Configurable Master and Slave modes
- Full-Duplex data transfer
- Mode fault error flag with CPU interrupt capability
- Double-buffered data register
- Serial clock with programmable polarity and phase
- LSB First or MSB First Data Transfer
- Interface to custom logic through 8-bit WISHBONE interface



Power-On-Reset Voltage Levels^{1, 2, 3, 4, 5}

Symbol	Parameter	Min.	Тур.	Max.	Units
V _{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and $V_{CCIO0})$	0.9	_	1.06	V
V _{PORUPEXT}	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	_	2.1	V
V _{PORDNBG}	Power-On-Reset ramp down trip point (band gap based circuit monitoring $V_{CCINT})$	0.75	_	0.93	V
V _{PORDNBGEXT}	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	_	1.33	V
V _{PORDNSRAM}	Power-On-Reset ramp down trip point (SRAM based circuit monitoring $V_{CCINT})$	_	0.6		V
V _{PORDNSRAMEXT}	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	_	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.

2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.

3. Note that V_{PORUP} (min.) and V_{PORDNBG} (max.) are in different process corners. For any given process corner V_{PORDNBG} (max.) is always 12.0 mV below V_{PORUP} (min.).

4. V_{PORUPEXT} is for HC devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.

5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Programming/Erase Specifications

Symbol	Parameter	Min.	Max. ¹	Units	
N _{PROGCYC}	Flash Programming cycles per t _{RETENTION}	—	10,000	Cycles	
	Flash functional programming cycles	— 100,000		Cycles	
	Data retention at 100 °C junction temperature	10	—	Years	
RETENTION	Data retention at 85 °C junction temperature	20	_	Teals	

1. Maximum Flash memory reads are limited to 7.5E13 cycles over the lifetime of the product.

Hot Socketing Specifications^{1, 2, 3}

Symbol	Parameter	Condition	Max.	Units	
I _{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	μΑ	

1. Insensitive to sequence of V_{CC} and V_{CCIO} . However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO} .

2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).

3. I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.

ESD Performance

Please refer to the MachXO2 Product Family Qualification Summary for complete qualification data, including ESD performance.



BLVDS

The MachXO2 family supports the BLVDS standard through emulation. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs. The input standard is supported by the LVDS differential input buffer. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS Multi-point Output Example



Table 3-2. BLVDS DC Conditions¹

Over Recommended	Operating	Conditions
	oporating	00110110110

		Non		
Symbol	Description	Zo = 45	Zo = 90	Units
Z _{OUT}	Output impedance	20	20	Ohms
R _S	Driver series resistance	80	80	Ohms
R _{TLEFT}	Left end termination	45	90	Ohms
R _{TRIGHT}	Right end termination	45	90	Ohms
V _{OH}	Output high voltage	1.376	1.480	V
V _{OL}	Output low voltage	1.124	1.020	V
V _{OD}	Output differential voltage	0.253	0.459	V
V _{CM}	Output common mode voltage	1.250	1.250	V
I _{DC}	DC output current	11.236	10.204	mA

1. For input buffer, see LVDS table.



			_	-6	_	5	_	4	
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
Generic DDR	X2 Outputs with Clock and Data	Centered at Pin Using P	CLK Pin	for Cloc	k Input –	GDDRX	2_TX.EC	LK.Cen	tered ^{9, 12}
t _{DVB}	Output Data Valid Before CLK Output		0.535	_	0.670	_	0.830	_	ns
t _{DVA}	Output Data Valid After CLK Output	MachXO2-640U,	0.535	_	0.670	_	0.830	_	ns
f _{DATA}	DDRX2 Serial Output Data Speed	MachXO2-1200/U and larger devices, top side only.		664	_	554	_	462	Mbps
f _{DDRX2}	DDRX2 ECLK Frequency (minimum limited by PLL)			332	_	277	_	231	MHz
f _{SCLK}	SCLK Frequency			166	—	139		116	MHz
Generic DDF	X4 Outputs with Clock and Data	Aligned at Pin Using P	CLK Pin	for Cloc	k Input	- GDDR	X4_TX.E	CLK.Ali	gned ^{9, 12}
t _{DIA}	Output Data Invalid After CLK Output		_	0.200	_	0.215	_	0.230	ns
t _{DIB}	Output Data Invalid Before CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only.		0.200	_	0.215	_	0.230	ns
f _{DATA}	DDRX4 Serial Output Data Speed			756	_	630	_	524	Mbps
f _{DDRX4}	DDRX4 ECLK Frequency		_	378	—	315	—	262	MHz
f _{SCLK}	SCLK Frequency		_	95	—	79		66	MHz
Generic DDF	X4 Outputs with Clock and Data	Centered at Pin Using Po	CLK Pin	for Cloc	k Input –	GDDRX	4_TX.EC	LK.Cen	tered ^{9, 12}
t _{DVB}	Output Data Valid Before CLK Output		0.455	_	0.570		0.710	—	ns
t _{DVA}	Output Data Valid After CLK Output	MachXO2-640U,	0.455	_	0.570		0.710	_	ns
f _{DATA}	DDRX4 Serial Output Data Speed	MachXO2-1200/U and larger devices, top side only.		756	_	630	_	524	Mbps
f _{DDRX4}	DDRX4 ECLK Frequency (minimum limited by PLL)	ony.		378	_	315	_	262	MHz
f _{SCLK}	SCLK Frequency		_	95	—	79	—	66	MHz
7:1 LVDS Ou	utputs - GDDR71_TX.ECLK.7:1	9, 12							
t _{DIB}	Output Data Invalid Before CLK Output		_	0.160	_	0.180		0.200	ns
t _{DIA}	Output Data Invalid After CLK Output	MachXO2-640U,		0.160	_	0.180	_	0.200	ns
f _{DATA}	DDR71 Serial Output Data Speed	MachXO2-6400, MachXO2-1200/U and larger devices, top side only.	_	756	_	630	_	524	Mbps
f _{DDR71}	DDR71 ECLK Frequency		_	378	_	315	_	262	MHz
fclkout	7:1 Output Clock Frequency (SCLK) (minimum limited by PLL)		_	108	_	90	_	75	MHz



			-	-3	_	2	_	·1	
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
LPDDR ^{9, 12}		•							
t _{DVADQ}	Input Data Valid After DQS Input		_	0.349	_	0.381	_	0.396	UI
t _{DVEDQ}	Input Data Hold After DQS Input		0.665	—	0.630	_	0.613	—	UI
t _{DQVBS}	Output Data Invalid Before DQS Output	MachXO2-1200/U	0.25	_	0.25	_	0.25	_	UI
t _{DQVAS}	Output Data Invalid After DQS Output	and larger devices, right side only. ¹³	0.25	_	0.25	_	0.25	_	UI
f _{DATA}	MEM LPDDR Serial Data Speed		_	120	_	110	_	96	Mbps
f _{SCLK}	SCLK Frequency		—	60	—	55		48	MHz
f _{LPDDR}	LPDDR Data Transfer Rate		0	120	0	110	0	96	Mbps
DDR ^{9, 12}		·			•				
t _{DVADQ}	Input Data Valid After DQS Input		_	0.347	_	0.374	_	0.393	UI
t _{DVEDQ}	Input Data Hold After DQS Input		0.665	_	0.637	_	0.616	—	UI
t _{DQVBS}	Output Data Invalid Before DQS Output	MachXO2-1200/U and larger devices,	0.25	_	0.25	_	0.25	—	UI
t _{DQVAS}	Output Data Invalid After DQS Output	right side only. ¹³	0.25	_	0.25	_	0.25	_	UI
f _{DATA}	MEM DDR Serial Data Speed			140	_	116		98	Mbps
f _{SCLK}	SCLK Frequency		—	70		58	—	49	MHz
f _{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps
DDR2 ^{9, 12}		•							
t _{DVADQ}	Input Data Valid After DQS Input		_	0.372	_	0.394	_	0.410	UI
t _{DVEDQ}	Input Data Hold After DQS Input		0.690	_	0.658	_	0.618	_	UI
t _{DQVBS}	Output Data Invalid Before DQS Output	MachXO2-1200/U	0.25	_	0.25	_	0.25	_	UI
t _{DQVAS}	Output Data Invalid After DQS Output	and larger devices, right side only. ¹³	0.25	_	0.25	_	0.25		UI
f _{DATA}	MEM DDR Serial Data Speed	1	—	140	—	116		98	Mbps
f _{SCLK}	SCLK Frequency	1	—	70	—	58		49	MHz
f _{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.

2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0 pf load, fast slew rate.

3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).

4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.

5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).

6. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03 \text{ ns})/2$.

7. The $t_{SU_{DEL}}$ and $t_{H_{DEL}}$ values use the SCLK_ZERHOLD default step size. Each step is 167 ps (-3), 182 ps (-2), 195 ps (-1).

8. This number for general purpose usage. Duty cycle tolerance is +/-10%.

9. Duty cycle is +/-5% for system usage.

10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.

11. High-speed DDR and LVDS not supported in SG32 (32-Pin QFN) packages.

12. Advance information for MachXO2 devices in 48 QFN packages.

13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.



MachXO2 Oscillator Output Frequency

Symbol	Parameter	Min.	Тур.	Max	Units
f	Oscillator Output Frequency (Commercial Grade Devices, 0 to 85°C)	125.685	133	140.315	MHz
TMAX	Oscillator Output Frequency (Industrial Grade Devices, –40 °C to 100 °C)	124.355	133	141.645	MHz
t _{DT}	Output Clock Duty Cycle	43	50	57	%
t _{OPJIT} 1	Output Clock Period Jitter	0.01	0.012	0.02	UIPP
t _{STABLEOSC}	STDBY Low to Oscillator Stable	0.01	0.05	0.1	μs

1. Output Clock Period Jitter specified at 133 MHz. The values for lower frequencies will be smaller UIPP. The typical value for 133 MHz is 95 ps and for 2.08 MHz the typical value is 1.54 ns.

MachXO2 Standby Mode Timing – HC/HE Devices

Symbol	Parameter	Device	Min.	Тур.	Max	Units
t _{PWRDN}	USERSTDBY High to Stop	All	_	_	9	ns
		LCMXO2-256		_		μs
		LCMXO2-640		_		μs
		LCMXO2-640U		_		μs
		LCMXO2-1200	20	_	50	μs
t _{PWRUP}	USERSTDBY Low to Power Up	LCMXO2-1200U				μs
		LCMXO2-2000		_		μs
		LCMXO2-2000U		_		μs
		LCMXO2-4000		_		μs
		LCMXO2-7000		_		μs
t _{WSTDBY}	USERSTDBY Pulse Width	All	18		—	ns



MachXO2 Standby Mode Timing – ZE Devices

Symbol	Parameter	Device	Min.	Тур.	Max	Units
t _{PWRDN}	USERSTDBY High to Stop	All	_	—	13	ns
		LCMXO2-256		—		μs
		LCMXO2-640		—		μs
	USERSTDBY Low to Power Up	LCMXO2-1200	20	—	50	μs
^t PWRUP		LCMXO2-2000		—		μs
		LCMXO2-4000		—		μs
		LCMXO2-7000		_		μs
t _{WSTDBY}	USERSTDBY Pulse Width	All	19			ns
t _{BNDGAPSTBL}	USERSTDBY High to Bandgap Stable	All		—	15	ns



Flash Download Time^{1, 2}

Symbol	Parameter	Device	Тур.	Units
		LCMXO2-256	0.6	ms
		LCMXO2-640	1.0	ms
		LCMXO2-640U	1.9	ms
		LCMXO2-1200	1.9	ms
t _{REFRESH}	POR to Device I/O Active	LCMXO2-1200U	1.4	ms
		LCMXO2-2000	1.4	ms
		LCMXO2-2000U	2.4	ms
		LCMXO2-4000	2.4	ms
		LCMXO2-7000	3.8	ms

1. Assumes sysMEM EBR initialized to an all zero pattern if they are used.

2. The Flash download time is measured starting from the maximum voltage of POR trip point.

JTAG Port Timing Specifications

Symbol	Parameter	Min.	Max.	Units
f _{MAX}	TCK clock frequency		25	MHz
t _{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t _{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t _{BTS}	TCK [BSCAN] setup time	10	—	ns
t _{BTH}	TCK [BSCAN] hold time	8	—	ns
t _{BTCO}	TAP controller falling edge of clock to valid output	_	10	ns
t _{BTCODIS}	TAP controller falling edge of clock to valid disable	_	10	ns
t _{BTCOEN}	TAP controller falling edge of clock to valid enable	_	10	ns
t _{BTCRS}	BSCAN test capture register setup time	8	—	ns
t _{BTCRH}	BSCAN test capture register hold time	20	—	ns
t _{BUTCO}	BSCAN test update register, falling edge of clock to valid output	_	25	ns
t _{BTUODIS}	BSCAN test update register, falling edge of clock to valid disable	_	25	ns
t _{BTUPOEN}	BSCAN test update register, falling edge of clock to valid enable		25	ns



Ultra Low Power Commercial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-256ZE-1SG32C	256	1.2 V	-1	Halogen-Free QFN	32	COM
LCMXO2-256ZE-2SG32C	256	1.2 V	-2	Halogen-Free QFN	32	COM
LCMXO2-256ZE-3SG32C	256	1.2 V	-3	Halogen-Free QFN	32	COM
LCMXO2-256ZE-1UMG64C	256	1.2 V	-1	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-2UMG64C	256	1.2 V	-2	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-3UMG64C	256	1.2 V	-3	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-1TG100C	256	1.2 V	-1	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-2TG100C	256	1.2 V	-2	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-3TG100C	256	1.2 V	-3	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-1MG132C	256	1.2 V	-1	Halogen-Free csBGA	132	COM
LCMXO2-256ZE-2MG132C	256	1.2 V	-2	Halogen-Free csBGA	132	COM
LCMXO2-256ZE-3MG132C	256	1.2 V	-3	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640ZE-1TG100C	640	1.2 V	-1	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-2TG100C	640	1.2 V	-2	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-3TG100C	640	1.2 V	-3	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-1MG132C	640	1.2 V	-1	Halogen-Free csBGA	132	COM
LCMXO2-640ZE-2MG132C	640	1.2 V	-2	Halogen-Free csBGA	132	COM
LCMXO2-640ZE-3MG132C	640	1.2 V	-3	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1SG32C	1280	1.2 V	-1	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-2SG32C	1280	1.2 V	-2	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-3SG32C	1280	1.2 V	-3	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-1TG100C	1280	1.2 V	-1	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-2TG100C	1280	1.2 V	-2	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-3TG100C	1280	1.2 V	-3	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-1MG132C	1280	1.2 V	-1	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-2MG132C	1280	1.2 V	-2	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-3MG132C	1280	1.2 V	-3	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-1TG144C	1280	1.2 V	-1	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-2TG144C	1280	1.2 V	-2	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-3TG144C	1280	1.2 V	-3	Halogen-Free TQFP	144	COM



Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200HC-4SG32C	1280	2.5 V / 3.3 V	-4	Halogen-Free QFN	32	COM
LCMXO2-1200HC-5SG32C	1280	2.5 V / 3.3 V	-5	Halogen-Free QFN	32	COM
LCMXO2-1200HC-6SG32C	1280	2.5 V / 3.3 V	-6	Halogen-Free QFN	32	COM
LCMXO2-1200HC-4TG100C	1280	2.5 V / 3.3 V	-4	Halogen-Free TQFP	100	COM
LCMXO2-1200HC-5TG100C	1280	2.5 V / 3.3 V	-5	Halogen-Free TQFP	100	COM
LCMXO2-1200HC-6TG100C	1280	2.5 V / 3.3 V	-6	Halogen-Free TQFP	100	COM
LCMXO2-1200HC-4MG132C	1280	2.5 V / 3.3 V	-4	Halogen-Free csBGA	132	COM
LCMXO2-1200HC-5MG132C	1280	2.5 V / 3.3 V	-5	Halogen-Free csBGA	132	COM
LCMXO2-1200HC-6MG132C	1280	2.5 V / 3.3 V	-6	Halogen-Free csBGA	132	COM
LCMXO2-1200HC-4TG144C	1280	2.5 V / 3.3 V	-4	Halogen-Free TQFP	144	COM
LCMXO2-1200HC-5TG144C	1280	2.5 V / 3.3 V	-5	Halogen-Free TQFP	144	COM
LCMXO2-1200HC-6TG144C	1280	2.5 V / 3.3 V	-6	Halogen-Free TQFP	144	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200UHC-4FTG256C	1280	2.5 V / 3.3 V	-4	Halogen-Free ftBGA	256	COM
LCMXO2-1200UHC-5FTG256C	1280	2.5 V / 3.3 V	-5	Halogen-Free ftBGA	256	COM
LCMXO2-1200UHC-6FTG256C	1280	2.5 V / 3.3 V	-6	Halogen-Free ftBGA	256	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000HC-4TG100C	2112	2.5 V / 3.3 V	-4	Halogen-Free TQFP	100	COM
LCMXO2-2000HC-5TG100C	2112	2.5 V / 3.3 V	-5	Halogen-Free TQFP	100	COM
LCMXO2-2000HC-6TG100C	2112	2.5 V / 3.3 V	-6	Halogen-Free TQFP	100	COM
LCMXO2-2000HC-4MG132C	2112	2.5 V / 3.3 V	-4	Halogen-Free csBGA	132	COM
LCMXO2-2000HC-5MG132C	2112	2.5 V / 3.3 V	-5	Halogen-Free csBGA	132	COM
LCMXO2-2000HC-6MG132C	2112	2.5 V / 3.3 V	-6	Halogen-Free csBGA	132	COM
LCMXO2-2000HC-4TG144C	2112	2.5 V / 3.3 V	-4	Halogen-Free TQFP	144	COM
LCMXO2-2000HC-5TG144C	2112	2.5 V / 3.3 V	-5	Halogen-Free TQFP	144	COM
LCMXO2-2000HC-6TG144C	2112	2.5 V / 3.3 V	-6	Halogen-Free TQFP	144	COM
LCMXO2-2000HC-4BG256C	2112	2.5 V / 3.3 V	-4	Halogen-Free caBGA	256	COM
LCMXO2-2000HC-5BG256C	2112	2.5 V / 3.3 V	-5	Halogen-Free caBGA	256	COM
LCMXO2-2000HC-6BG256C	2112	2.5 V / 3.3 V	-6	Halogen-Free caBGA	256	COM
LCMXO2-2000HC-4FTG256C	2112	2.5 V / 3.3 V	-4	Halogen-Free ftBGA	256	COM
LCMXO2-2000HC-5FTG256C	2112	2.5 V / 3.3 V	-5	Halogen-Free ftBGA	256	COM
LCMXO2-2000HC-6FTG256C	2112	2.5 V / 3.3 V	-6	Halogen-Free ftBGA	256	COM



Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000ZE-1QN84I	4320	1.2 V	-1	Halogen-Free QFN	84	IND
LCMXO2-4000ZE-2QN84I	4320	1.2 V	-2	Halogen-Free QFN	84	IND
LCMXO2-4000ZE-3QN84I	4320	1.2 V	-3	Halogen-Free QFN	84	IND
LCMXO2-4000ZE-1MG132I	4320	1.2 V	-1	Halogen-Free csBGA	132	IND
LCMXO2-4000ZE-2MG132I	4320	1.2 V	-2	Halogen-Free csBGA	132	IND
LCMXO2-4000ZE-3MG132I	4320	1.2 V	-3	Halogen-Free csBGA	132	IND
LCMXO2-4000ZE-1TG144I	4320	1.2 V	-1	Halogen-Free TQFP	144	IND
LCMXO2-4000ZE-2TG144I	4320	1.2 V	-2	Halogen-Free TQFP	144	IND
LCMXO2-4000ZE-3TG144I	4320	1.2 V	-3	Halogen-Free TQFP	144	IND
LCMXO2-4000ZE-1BG256I	4320	1.2 V	-1	Halogen-Free caBGA	256	IND
LCMXO2-4000ZE-2BG256I	4320	1.2 V	-2	Halogen-Free caBGA	256	IND
LCMXO2-4000ZE-3BG256I	4320	1.2 V	-3	Halogen-Free caBGA	256	IND
LCMXO2-4000ZE-1FTG256I	4320	1.2 V	-1	Halogen-Free ftBGA	256	IND
LCMXO2-4000ZE-2FTG256I	4320	1.2 V	-2	Halogen-Free ftBGA	256	IND
LCMXO2-4000ZE-3FTG256I	4320	1.2 V	-3	Halogen-Free ftBGA	256	IND
LCMXO2-4000ZE-1BG332I	4320	1.2 V	-1	Halogen-Free caBGA	332	IND
LCMXO2-4000ZE-2BG332I	4320	1.2 V	-2	Halogen-Free caBGA	332	IND
LCMXO2-4000ZE-3BG332I	4320	1.2 V	-3	Halogen-Free caBGA	332	IND
LCMXO2-4000ZE-1FG484I	4320	1.2 V	-1	Halogen-Free fpBGA	484	IND
LCMXO2-4000ZE-2FG484I	4320	1.2 V	-2	Halogen-Free fpBGA	484	IND
LCMXO2-4000ZE-3FG484I	4320	1.2 V	-3	Halogen-Free fpBGA	484	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000ZE-1TG144I	6864	1.2 V	-1	Halogen-Free TQFP	144	IND
LCMXO2-7000ZE-2TG144I	6864	1.2 V	-2	Halogen-Free TQFP	144	IND
LCMXO2-7000ZE-3TG144I	6864	1.2 V	-3	Halogen-Free TQFP	144	IND
LCMXO2-7000ZE-1BG256I	6864	1.2 V	-1	Halogen-Free caBGA	256	IND
LCMXO2-7000ZE-2BG256I	6864	1.2 V	-2	Halogen-Free caBGA	256	IND
LCMXO2-7000ZE-3BG256I	6864	1.2 V	-3	Halogen-Free caBGA	256	IND
LCMXO2-7000ZE-1FTG256I	6864	1.2 V	-1	Halogen-Free ftBGA	256	IND
LCMXO2-7000ZE-2FTG256I	6864	1.2 V	-2	Halogen-Free ftBGA	256	IND
LCMXO2-7000ZE-3FTG256I	6864	1.2 V	-3	Halogen-Free ftBGA	256	IND
LCMXO2-7000ZE-1BG332I	6864	1.2 V	-1	Halogen-Free caBGA	332	IND
LCMXO2-7000ZE-2BG332I	6864	1.2 V	-2	Halogen-Free caBGA	332	IND
LCMXO2-7000ZE-3BG332I	6864	1.2 V	-3	Halogen-Free caBGA	332	IND
LCMXO2-7000ZE-1FG484I	6864	1.2 V	-1	Halogen-Free fpBGA	484	IND
LCMXO2-7000ZE-2FG484I	6864	1.2 V	-2	Halogen-Free fpBGA	484	IND
LCMXO2-7000ZE-3FG484I	6864	1.2 V	-3	Halogen-Free fpBGA	484	IND



High-Performance Industrial Grade Devices with Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-256HC-4SG32I	256	2.5 V / 3.3 V	-4	Halogen-Free QFN	32	IND
LCMXO2-256HC-5SG32I	256	2.5 V / 3.3 V	-5	Halogen-Free QFN	32	IND
LCMXO2-256HC-6SG32I	256	2.5 V / 3.3 V	-6	Halogen-Free QFN	32	IND
LCMXO2-256HC-4SG48I	256	2.5 V / 3.3 V	-4	Halogen-Free QFN	48	IND
LCMXO2-256HC-5SG48I	256	2.5 V / 3.3 V	-5	Halogen-Free QFN	48	IND
LCMXO2-256HC-6SG48I	256	2.5 V / 3.3 V	-6	Halogen-Free QFN	48	IND
LCMXO2-256HC-4UMG64I	256	2.5 V / 3.3 V	-4	Halogen-Free ucBGA	64	IND
LCMXO2-256HC-5UMG64I	256	2.5 V / 3.3 V	-5	Halogen-Free ucBGA	64	IND
LCMXO2-256HC-6UMG64I	256	2.5 V / 3.3 V	-6	Halogen-Free ucBGA	64	IND
LCMXO2-256HC-4TG100I	256	2.5 V / 3.3 V	-4	Halogen-Free TQFP	100	IND
LCMXO2-256HC-5TG100I	256	2.5 V / 3.3 V	-5	Halogen-Free TQFP	100	IND
LCMXO2-256HC-6TG100I	256	2.5 V / 3.3 V	-6	Halogen-Free TQFP	100	IND
LCMXO2-256HC-4MG132I	256	2.5 V / 3.3 V	-4	Halogen-Free csBGA	132	IND
LCMXO2-256HC-5MG132I	256	2.5 V / 3.3 V	-5	Halogen-Free csBGA	132	IND
LCMXO2-256HC-6MG132I	256	2.5 V / 3.3 V	-6	Halogen-Free csBGA	132	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640HC-4SG48I	640	2.5 V / 3.3 V	-4	Halogen-Free QFN	48	IND
LCMXO2-640HC-5SG48I	640	2.5 V / 3.3 V	-5	Halogen-Free QFN	48	IND
LCMXO2-640HC-6SG48I	640	2.5 V / 3.3 V	-6	Halogen-Free QFN	48	IND
LCMXO2-640HC-4TG100I	640	2.5 V / 3.3 V	-4	Halogen-Free TQFP	100	IND
LCMXO2-640HC-5TG100I	640	2.5 V / 3.3 V	-5	Halogen-Free TQFP	100	IND
LCMXO2-640HC-6TG100I	640	2.5 V / 3.3 V	-6	Halogen-Free TQFP	100	IND
LCMXO2-640HC-4MG132I	640	2.5 V / 3.3 V	-4	Halogen-Free csBGA	132	IND
LCMXO2-640HC-5MG132I	640	2.5 V / 3.3 V	-5	Halogen-Free csBGA	132	IND
LCMXO2-640HC-6MG132I	640	2.5 V / 3.3 V	-6	Halogen-Free csBGA	132	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640UHC-4TG144I	640	2.5 V / 3.3 V	-4	Halogen-Free TQFP	144	IND
LCMXO2-640UHC-5TG144I	640	2.5 V / 3.3 V	-5	Halogen-Free TQFP	144	IND
LCMXO2-640UHC-6TG144I	640	2.5 V / 3.3 V	-6	Halogen-Free TQFP	144	IND



MachXO2 Family Data Sheet Revision History

March 2017

Data Sheet DS1035

Date	Version	Section	Change Summary
March 2017	3.3	DC and Switching Characteristics	Updated the Absolute Maximum Ratings section. Added standards.
			Updated the sysIO Recommended Operating Conditions section. Added standards.
			Updated the sysIO Single-Ended DC Electrical Characteristics sec- tion. Added standards.
			Updated the MachXO2 External Switching Characteristics – HC/HE Devices section. Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, the D_{VB} and the D_{VA} parameters were changed to D_{IB} and D_{IA} . The parameter descriptions were also modified.
			Updated the MachXO2 External Switching Characteristics – ZE Devices section. Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, the D_{VB} and the D_{VA} parameters were changed to D_{IB} and D_{IA} . The parameter descriptions were also modified.
			Updated the sysCONFIG Port Timing Specifications section. Corrected the t_{INITL} units from ns to μ s.
		Pinout Information	Updated the Signal Descriptions section. Revised the descriptions of the PROGRAMN, INITN, and DONE signals.
	Ordering Information		Updated the Pinout Information Summary section. Added footnote to MachXO2-1200 32 QFN.
		Updated the MachXO2 Part Number Description section. Corrected the MG184, BG256, FTG256 package information. Added "(0.8 mm Pitch)" to BG332.	
			Updated the Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging section. — Updated LCMXO2-1200ZE-1UWG25ITR50 footnote. — Corrected footnote numbering typo. — Added the LCMXO2-2000ZE-1UWG49ITR50 and LCMXO2- 2000ZE-1UWG49ITR1K part numbers. Updated/added footnote/s.

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